

Data sheet acquired from Harris Semiconductor

CMOS Strobed Hex Inverter/Buffer

High-Voltage Types (20-Volt Rating)

buffers with 3-state outputs. A logic "1" on the OUTPUT DISABLE input produces a high-impedance state in all six outputs. This feature permits common busing of the outputs, thus simplifying system design. A Logic "1" on the INHIBIT input switches all six outputs to logic "0" if the OUTPUT DISABLE input is a logic "0". This device is capable of driving two standard TTL loads, which is equivalent to six times the JEDEC "B"-series IOL standard.

The CD4502B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic package (E suffix), and in chip form (H suffix). This device is similar to the MC14502.

MAXIMUM RATINGS, Absolute-Maximum Values:

CD4502B Types

12

DISABLE

Features:

- 2 TTL-load output drive capability
- 3-state outputs
- Common output-disable control
- Inhibit control
- 100% tested for quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Maximum input current of 1 µA at 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Meets all requirements of JEDEC Tentative Standard No. 138, "Standard Specifications for Description of 'B' Series CMOS Devices"
- Noise margin (full package-temperature range) =

1 V at V_{DD} = 5 V 2 V at V_{DD} = 10 V 2.5 V at V_{DD} = 15 V

Applications:

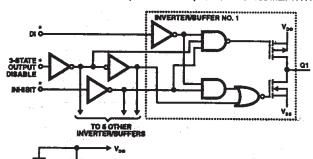
- 3-state hex inverter for interfacing IC's with data buses
- COS/MOS to TTL hex buffer

AMBIENT TEMPERATURE (T_A): 25°C. | GATE-TO-SOURCE VOLTAGE (V_{QS}): 15 V. | GATE-TO-SOURCE VOLTAGE (V_{QS}): 15 V. | GATE-TO-SOURCE VOLTAGE (V_{QS}): 15 V.

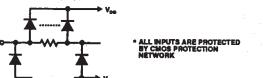
FUNCTIONAL DIAGRAM

Fig.2 - Typical output low (sink) current characteristics.

DC SUPPLY-VOLTAGE RANGE, (V_{DD}) Voltages referenced to V_{SS} Terminal) -0.5V to +20V INPUT VOLTAGE RANGE, ALL INPUTS -0.5V to V_{DD} +0.5V DC INPUT CURRENT, ANY ONE INPUT ±10mA POWER DISSIPATION PER PACKAGE (P_D): For $T_A = -55^{\circ}$ C to +100°C 500mW For $T_A = +100^{\circ}$ C to +125°C Derate Linearity at 12mW/°C to 200mW DEVICE DISSIPATION PER OUTPUT TRANSISTOR FOR $T_A = FULL$ PACKAGE-TEMPERATURE RANGE (All Package Types) 0PERATING-TEMPERATURE RANGE (T_A) 55°C to +125°C STORAGE TEMPERATURE RANGE (T_{atg}) -65°C to +150°C LÉAD TEMPERATURE (DURING SOLDERING): At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max +285°C

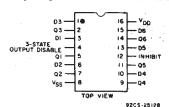


TRUTH TABLE							
DISABLE	INHIBIT	Dn	Qη				
0	0	0	1				
0	0	1	0				
0	4 5	х	0				
1	х	Х	Z				



Logic 0 = Low
Z = High Impedance
X = Don't Care
Logic 1 = High

Fig. 1 — Logic diagram of 1 of 6 identical inverter/buffers.



TERMINAL ASSIGNMENT

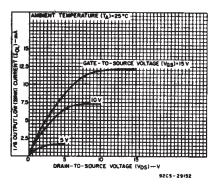


Fig.3 - Minimum output low (sink) current characteristics.

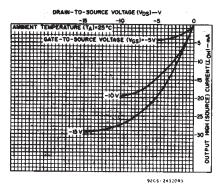


Fig.4 - Typical output high (source) current characteristics.

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

LIM	1101170	
Min.	Max.	UNITS
3	18	V

STATIC ELECTRICAL CHARACTERISTICS

CHARACTER- ISTIC	CONDITIONS			LIMITS AT INDICATED TE						UNITS		
	Vo (V)	V _{IN} (v)	V _{DD} (V)	-55	-40	+85	+125	Min.	+25 Typ.	Max.	ur±ts Link	
Ouissant Daviss	_	0,5	5	1	1	30	30	_	0.02	1	μА	
Ouiescent Device Current, IDD Max.		0,10	10	2	2	60	60		0.02	2		
		0,15	15	4	4	120	120		0.02	4		
		0,20	20	20	20	600	600		0.04	20		
Output Low	0.4	0,5	5	3.84	3.66	2,52	2.16	3.06	6			
(Sink) Current	0.5	0,10	10	9.6	9	6.6	5.4	7.8	15.6	-	7	
IOL Min.	1.5	0.15	15	25.2	24	16.8	14.4	20.4	40.8	_		
Output High	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	_	mA	
(Source)	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-		
Current,	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	_		
IOH Min.	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-		
Output Voltage:	-	0,5	5	0.05			_	0 .	0.05			
Low-Level,	-	0,10	10	0.05				0	0.05	.		
VOL Max.		0,15	15	0.05			_	0	0.05	_v		
Output Voltage:	_	0,5	5	4.95			4.95	5	-	ľ		
High-Level,	-	0,10	10	9.95			9.95	10	-			
VOH Min.	-	0,15	15	14.95			14.95	15		1		
Input Low Voltage, VIL Max.	0.5, 4.5		5	1.5			_		1.5			
	1, 9	-	10	3				-	_	3		
	15, 13.5	-	15	4			_	<u> </u>	4	_v		
Input High	4.5	-	5	3.5				3.5	_]	
Voltage, VIH Min.	9	-	10	7			7		_ —			
	13.5	-	15			11		11	 	_		
Input Current IJN Max.		0,18	18	±0.1	±0.1	±1	±1	-	±10 ⁻⁵	±0.1	μА	
3-State Output Leakage Current IOUT Max.	0,18	0,18	18	±0.4	±0.4	±12	±12		±10~4	±0.4	μΑ	

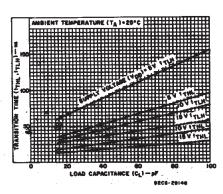


Fig.8 - Typical transition time as a function of load capacitance.

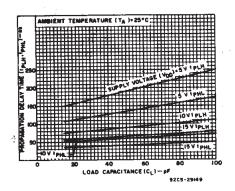


Fig.9 — Typical propagation-dalay time as a function of load capacitance.

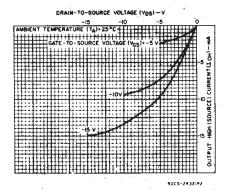


Fig.5 — Minimum output high (source) current characteristics.

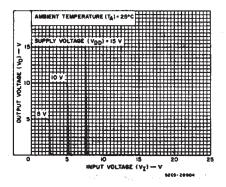


Fig.6 — Typical voltage transfer characteristics.

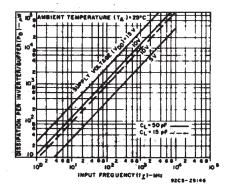


Fig.7 — Typical power dissipation as a function of input frequency.

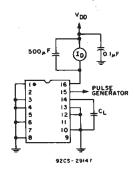


Fig. 10 - Power-dissipation test circuit.

DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = 25°C; Input t_r, t_f = 20 ns, C_L = 50 pF, R_L = 200 K Ω Unless otherwise specified.

CHARACTERISTIC	TEST CONDITIONS		LIMITS		UNITS
		V _{DD} (V)	TYP	MAX	ONTS
Data or Inhibit Delay Times: High to Low, tpHL		5 10 15	135 60 40	270 120 80	
Low to High, tPLH		5 10 15	190 90 65	380 180 130	ns
Disable Delay Times: R_L =1 K Ω Output High to High Impedance, t_{PHZ}		5 10 15	60 40 30	120 80 60	* *
High-Impedance to Output High, tPZH	Sac 51 - 44	5 10 15	110 50 40	220 100 80	ns
Output Low to High Impedance, tPLZ	See Fig. 14	5 10 15	125 65 55	250 130 110	713
High Impedance to Output Low, tPZL		5 10 15	125 55 40	250 110 80	
Transition Times: Low to High, t _{TLH}		5 10 15	100 50 40	200 100 80	ns
High to Low, tTHL		5 10 15	60 30 20	120 60 40	113
Input Capacitance, CIN	Any Input		5	7.5	pF
Output Capacitance, COUT	ŀ		7-8	15	pF

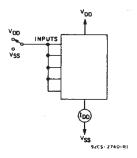


Fig. 11 — Quiescent-device-current test circuit.

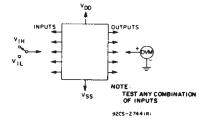


Fig. 12 - Input-voltage test circuit.

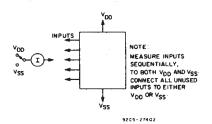


Fig. 13 - Input leakage current test circuit.

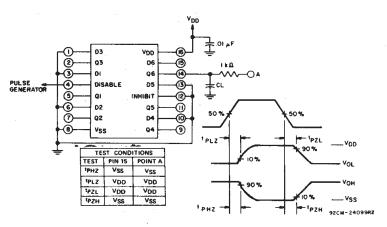
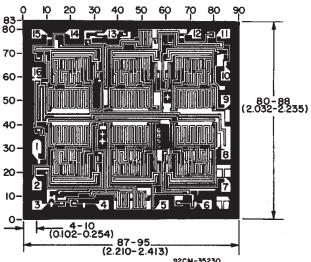


Fig. 14 — Disable delay times test circuit and waveforms.



Dimensions and Pad Layout for CD4502BH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils $(10^{-3} \, \text{inch.})$

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